SUMMARY CHART OF RTA MACHINES

RTA-NoMetal ANNEALSYS

Location: ICL

PTC: CMOS clean processes
Wafer size: Up to 6". / Cold walls system.
Temperature Range: 300C – 1100 C / Pyrometer control
100C – 1000 C / Thermocouple control
Maximum ramp up: on Silicon wafer : 150C/sec
on SiC susceptor: 30C/sec
Gases: N2 & O2 installed; (FG , NH3 and vacuum capable)

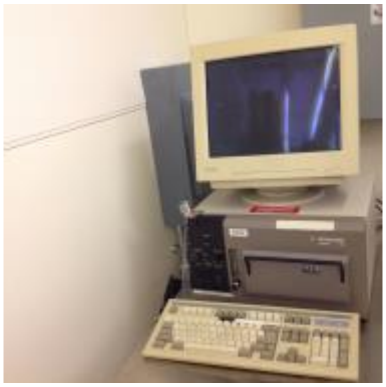
RTA-Pieces ANNEALSYS

LOCATION: ICL

PTC: Au labeled machine: No photoresist or organic traces allowed.
Wafers size: Up to 2". / Hot wall system.
Temperature Range: 100C – 1000 C, under Thermocouple control.
Maximum ramp up: 30C /sec with SiC susceptor.
Gases: N2, NH3 & FG. Vacuum

RTA-Metal AG-Associates 410

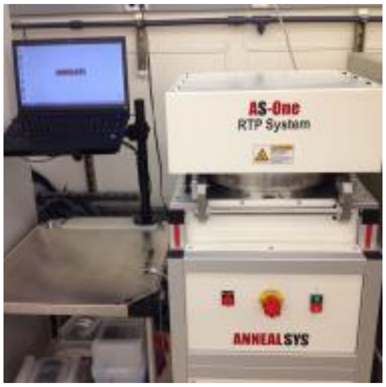
Location: ICL



PTC: CMOS metals only on Si, SiGe, Ge, Quartz, SiC.
Wafers size: Up to 6” / Hot wall system.
Temperature Range: 350C - 900C. TC control.
Gases: N2

RTA-HIT ANNEALSYS

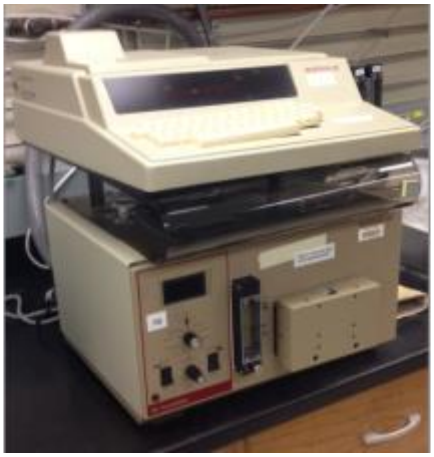
Location: TRL



PTC: Au labeled machine. No photoresist or organic traces allowed.
Wafers size: Up to 6”. / Cold walls system.
Temperature range: 400 C – 1200C : under Pyrometer control
100 C - 1000C ; under Thermocouple control
Maximum ramp up: on Silicon wafers : 150C /sec
on SiC susceptor: 30C /sec.
Gases: N2 & vacuum installed; (O2 , FG & NH3 capable)

RTA –EML   AG Associates 210

Location EML



PTC : No process approval needed; material safety compliance required.
Wafer size: UP to 4” / Hot walls system.
Temperature range: 100 C- 800C under Thermocouple control.
Ramp up: 50C/sec
Gases: N2, O2 & FG